

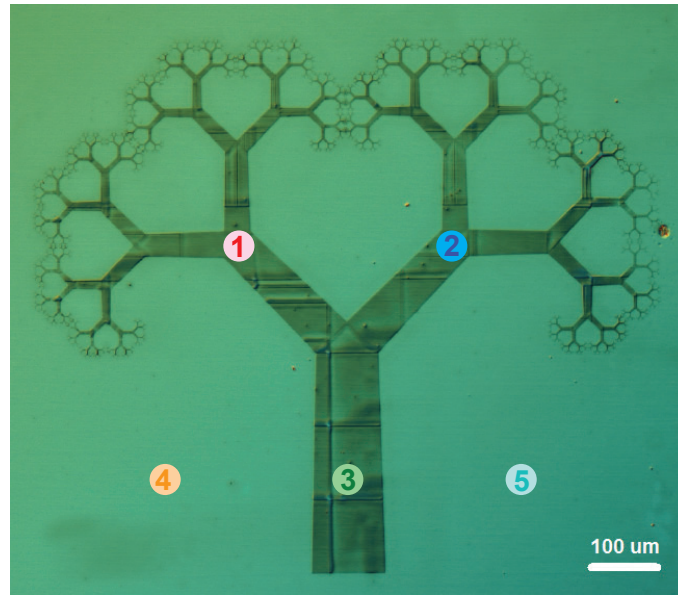
SUPPORTING INFORMATION

E-Beam Nanostructuring and Direct Click Biofunctionalization of Thiol-Ene Resist

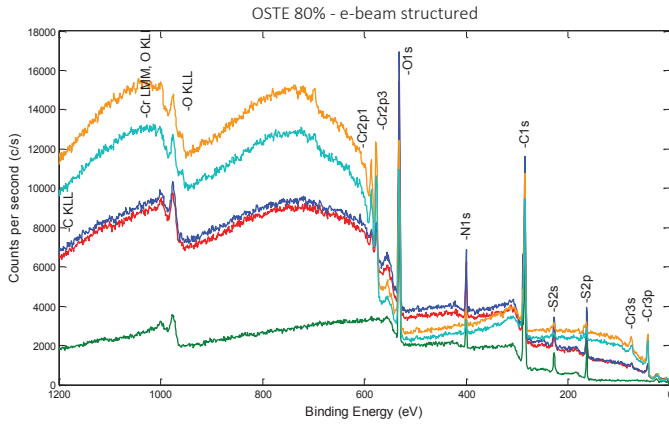
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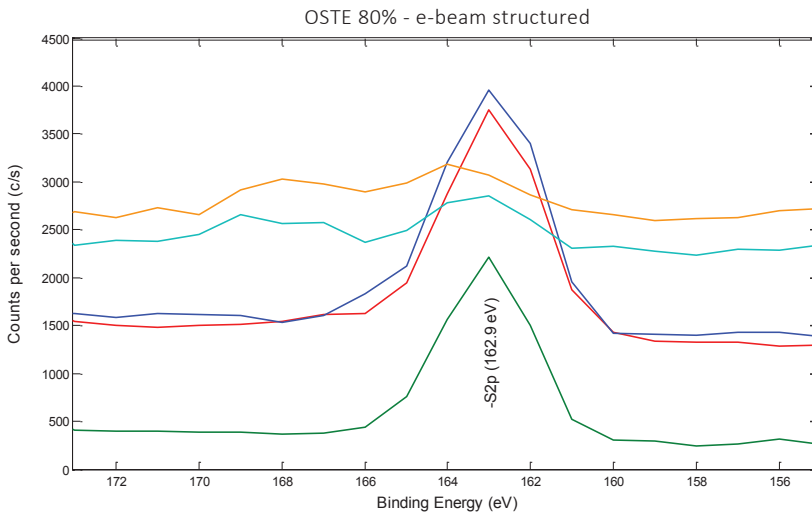
(a)



(b)

Positions	Atomic Percent (at.%)				
	C	N	O	S	Cr
1	57.6	7.8	27.8	4.5	2.4
2	58.2	7.4	28.3	4.2	1.8
3	60.7	8.4	25.4	5.2	0.5
4	57.4	2.7	29.4	1.8	8.8
5	56.0	3.1	30.4	1.6	8.9

(c)



(d)

Positions	Peak position (eV)	Area
1	163.0	7220
2	162.7	7445
3	163.0	5000
4	163.7	2215
5	163.4	2150

(e)

FIG. S1: XPS analysis of the thiol-ene e-beam resist prior to protein patterning. a) Photograph of an e-beam exposed fractal tree pattern in the thiol-ene e-beam resist. The numbers 1-5 indicate the positions at which the spectrum was measured. b) XPS spectrum at the five positions. c) The elemental state at the selected positions. d) Zoom in of the photoelectric spectrum around the thiol characteristic peak. e) Comparison of the area under the thiol-peak among the five positions.

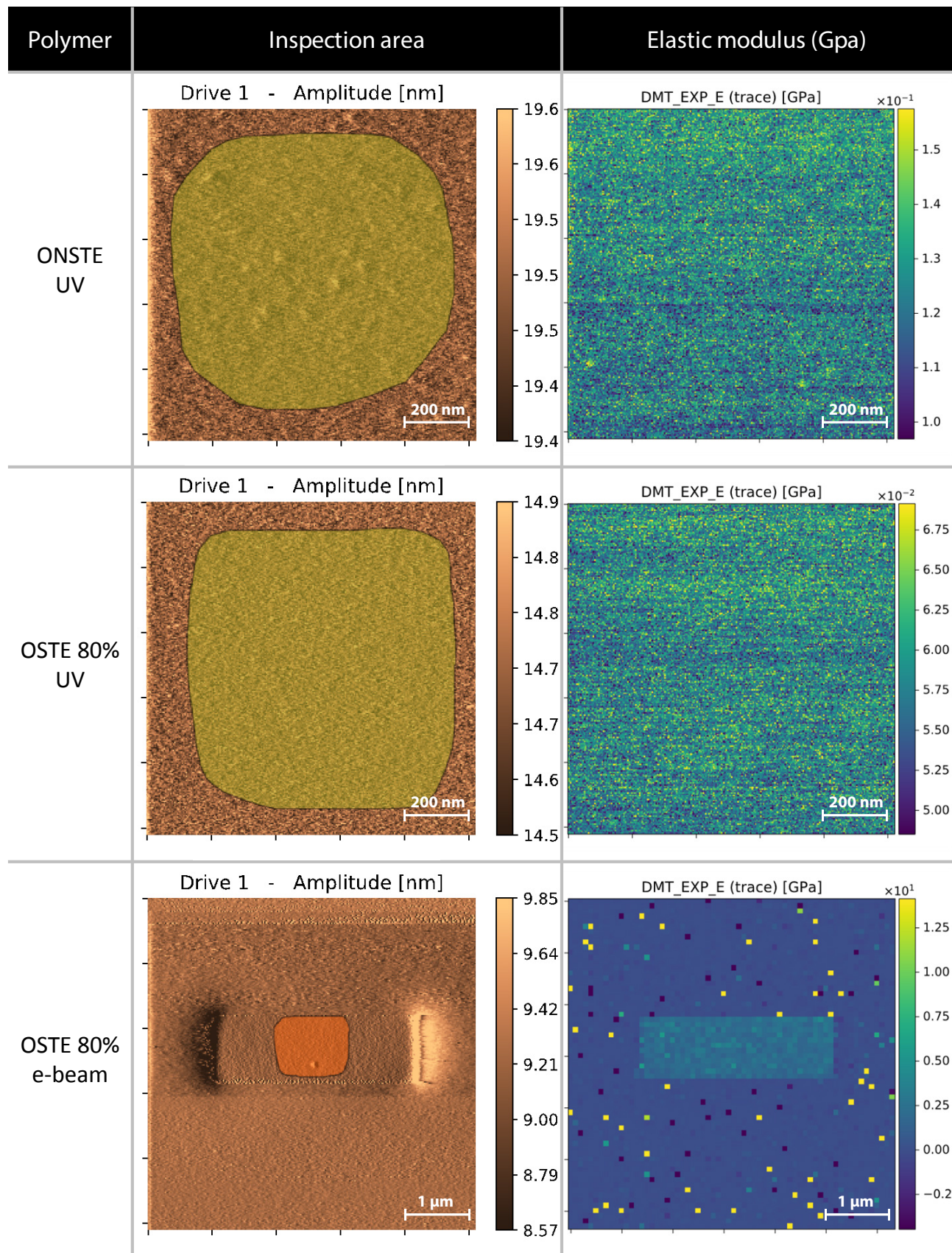


FIG. S2: Intermodulation AFM analysis of thiol-ene based resin after UV flood exposure/e-beam structuring: The colour graphs of the elastic modulus (right) are correlated to the AFM scanned areas (amplitude images on left). The average E-modulus for the selected areas of $\approx 1\mu\text{m}^2$ (drawn yellow parts on inspection areas) is approximately equal to 130 MPa for UV-cured on-stoichiometric thiol-ene (ONSTE), 60 MPa for UV-cured off-stoichiometric thiol-ene of 80% thiol excess (OSTE 80% UV) and 3 GPa for e-beam structured off-stoichiometric thiol-ene of 80% thiol excess (OSTE 80% e-beam).